Abstracts

Design and Performance of K-Band Power GaAs FETs on Matched Carriers

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L. Rosenheck, S. Dow, C. Berglund and M. Stevens. "Design and Performance of K-Band Power GaAs FETs on Matched Carriers." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 270-272.

Experimental relationships between the gain of K-band GaAs power FETs and the device geometries. Output powers as high as 1100mW with 4.3dB associated gain at 20.2 GHz have been measured. Matched carrier performance on both fused silica and sapphire is described.

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